

212771US-22 PCT

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF: :
MASASHI KAWASKI ET AL : ATTN: APPLICATION DIVISION
SERIAL NO: NEW US PCT APPLN :
(Based on PCT/JP00/01736)
FILED: HEREWITH : EXAMINER:
FOR: SEMICONDUCTOR DEVICE :

#L/A
15 Mar 02
P. Talley

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Prior to examination on the merits, please amend the above-identified application as follows:

IN THE CLAIMS

Please cancel Claims 1-10.

Please add new Claims 11-30 as follows:

11. (New) A semiconductor device comprising,
a substrate containing a material of formula LnABO_4 or $\text{LnAO}_3(\text{BO})_n$ for basic
structure,
wherein,
Ln is a rare earth element,
A is selected from the group consisting of Fe, Ga and Al,
B is selected from the group consisting of Mn, Co, Fe, Zn, Cu, Mg and Cd,

Al (sub) B

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